

In the Claims

Claims 1-97 are canceled.

98. [Previously Presented] A method of processing a workpiece comprising:
receiving a first workpiece and a second workpiece within a workpiece processing apparatus configured to form a semiconductor device using the first workpiece;
processing the first workpiece within the workpiece processing apparatus to form the semiconductor device; and
communicating signals intermediate the second workpiece and the workpiece processing apparatus.

99. [Previously Presented] The method in accordance with claim 98 further comprising electrically coupling the second workpiece and the workpiece processing apparatus.

100. [Previously Presented] The method in accordance with claim 99 wherein the coupling comprises contacting circuitry of the second workpiece and circuitry of the apparatus.

101. [Previously Presented] The method in accordance with claim 98 further comprising:
supporting the second workpiece using a workpiece holder of the workpiece processing apparatus; and

coupling circuitry of the second workpiece and circuitry of the workpiece holder at a surface of the second workpiece and a surface of the workpiece holder.

102. [Previously Presented] The method in accordance with claim 98 wherein the receiving comprises receiving the first workpiece comprising a semiconductive wafer.

103. [Previously Presented] The method in accordance with claim 98 further comprising altering the processing responsive to the communicating.

104. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating during the processing.

105. [Previously Presented] The method in accordance with claim 98 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

106. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information.

107. [Previously Presented] The method in accordance with claim 98 wherein the communicating comprises communicating the signals comprising information regarding the processing.

108. [Previously Presented] A method of communicating signals with respect to a wafer comprising:

providing a workpiece holder;

supporting a wafer using the workpiece holder;

coupling circuitry of the wafer with circuitry of the workpiece holder;

communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder; and

wherein the communicating comprises communicating the signals comprising information regarding process conditions of a workpiece processing apparatus.

109. [Previously Presented] The method in accordance with claim 108 wherein the providing the wafer comprises providing a semiconductive wafer.

110. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at a surface of the wafer and a surface of the workpiece holder.

111. [Previously Presented] The method in accordance with claim 108 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

112. [Previously Presented] The method in accordance with claim 108 wherein the communicating comprises communicating using an intermediate member.

113. Canceled.

114. Canceled.

115. [Previously Presented] A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to form a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece;

receiving the signals within the workpiece processing apparatus from the workpiece;

and

wherein the communicating comprises communicating the signals comprising process signals comprising information regarding process conditions of the workpiece processing apparatus used to form the semiconductor device.

116. [Previously Presented] The method in accordance with claim 115 further comprising coupling circuitry of the workpiece with circuitry of the workpiece processing apparatus.

117. [Previously Presented] The method in accordance with claim 116 wherein the coupling comprises contacting the circuitry of the workpiece with the circuitry of the workpiece processing apparatus.

118. [Previously Presented] The method in accordance with claim 116 further comprising breaking the coupling of the circuitry of the workpiece and the circuitry of the workpiece processing apparatus.

119. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder, and wherein the receiving comprises receiving using the workpiece holder.

120. [Previously Presented] The method in accordance with claim 119 further comprising coupling circuitry of the workpiece and circuitry of the workpiece holder at a surface of the workpiece and a surface of the workpiece holder.

121. [Previously Presented] The method in accordance with claim 115 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder and an intermediate member, and wherein the receiving comprises receiving using the workpiece holder and the intermediate member.

122. [Previously Presented] The method in accordance with claim 115 wherein the providing the workpiece comprises providing a semiconductive wafer.

Claims 123-130 are canceled.

131. [Previously Presented] The method in accordance with claim 115 further comprises exposing the workpiece to process conditions configured to form the semiconductor device.

132. Canceled.

133. [Previously Presented] The method in accordance with claim 115 wherein the receiving comprises receiving the signals comprising information using circuitry of the workpiece processing apparatus.

134. Canceled.

135. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising the information regarding a temperature of a surface of the workpiece.

136. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising the information regarding temperature information at a plurality of different positions of a surface of the workpiece.

137. [Previously Presented] A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to form a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece;

receiving the signals within the workpiece processing apparatus from the workpiece;

and

wherein the communicating comprises communicating the signals comprising process signals comprising information regarding a temperature of a surface of the workpiece.

138. [Previously Presented] A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to form a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece;

receiving the signals within the workpiece processing apparatus from the workpiece;

and

wherein the communicating comprises communicating the signals comprising process signals comprising information regarding temperature information at a plurality of different positions of a surface of the workpiece.

139. [Previously Presented] The method in accordance with claim 115 wherein the communicating comprises communicating the signals comprising process signals comprising information regarding temperature information at a plurality of different positions of a surface of the workpiece.